



PATENT
Attorney Docket No.: NICHIA-00700

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	Group Art Unit:
)	
Shuji Nakamura <i>et al.</i>)	Examiner:
)	
Serial No.: 09/463,643)	<u>INFORMATION DISCLOSURE</u>
)	<u>STATEMENT</u>
)	
Filed: January 25, 2000)	
)	260 Sheridan Avenue, Suite 420
For: NITRIDE SEMICONDUCTOR)	Palo Alto, California 94306
DEVICE)	(650)833-0160

#8
4-11-01
T. Flowers

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The citations listed below, copies attached, may be material to the examination of the above-identified application, and are therefore submitted in compliance with the duty of disclosure defined in 37 C.F.R. §§ 1.56 and 1.97. The Examiner is requested to make these citations of official record in this application.

Applicants have become aware of the following printed publications which may be material to the examination of this application:

- Japanese Publication No.: 04144294;
- Japanese Publication No.: 09180998;
- Japanese Publication No.: 09246651;
- Japanese Publication No.: 09260772;
- Japanese Publication No.: 09293935;
- Japanese Publication No.: 10242565;
- Japanese Publication No.: 10256645;
- Japanese Publication No.: 10270792;
- Japanese Publication No.: 10290027;

RECEIVED
SEP 13 2000
TECHNOLOGY CENTER 2800

CERTIFICATE OF MAILING (37 CFR § 1.8(a))
I hereby certify that this paper (along with any referred to as being attached or enclosed) is being deposited with the U.S. Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the: Assistant Commissioner for Patents, Washington D.C. 20231

HAVERSTOCK & OWENS LLP

Date: 9/8/00 By: Carleen O'Neil

- Japanese Publication No.: 10294529;
- Japanese Publication No.: 10321962;
- Japanese Publication No.: 11040893;
- Japanese Publication No.: 2000-31599;
- German Publication No.: DE 196 48 955A1; and
- "InGaN/GaN/AlGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate," Shuji Nakamura et al., Applied Physics Letter, Vol. 72, No. 2, January 12, 1998.

This Information Disclosure Statement under 37 C.F.R. §§ 1.56 and 1.97 is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that anyone or more of these citations constitutes prior art.

Respectfully submitted,

HAVERSTOCK & OWENS LLP

Dated: 9/8/00

By: 

Thomas B. Haverstock

Reg. No.: 32,571

Attorneys for Applicants